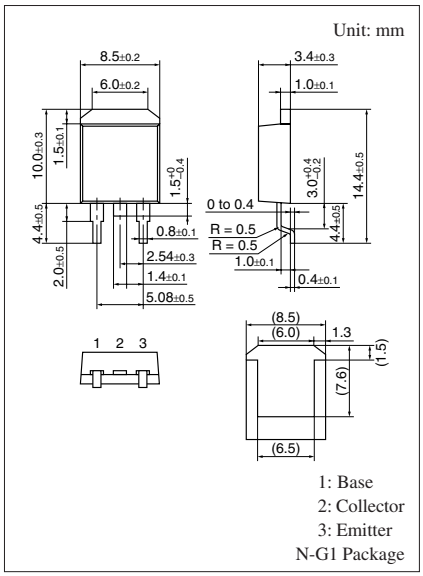
2SB0937 (2SB937), 2SB0937A (2SB937A)

Silicon PNP epitaxial planar type Darlington

For power amplification and switching
Complementary to 2SD1260, 2SD1260A

■ Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

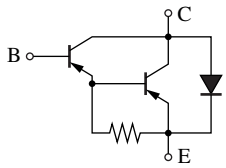


Note) Self-supported type package is also prepared.

■ Absolute Maximum Ratings $T_C = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0937	V_{CBO}	−60	V
	2SB0937A		−80	
Collector-emitter voltage (Base open)	2SB0937	V_{CEO}	−60	V
	2SB0937A		−80	
Emitter-base voltage (Collector open)		V_{EBO}	−5	V
Collector current		I_C	−2	A
Peak collector current		I_{CP}	−4	A
Collector power dissipation		P_C	35	W
	$T_a = 25°C$		1.3	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

Internal Connection



■ Electrical Characteristics $T_C = 25°C \pm 3°C$

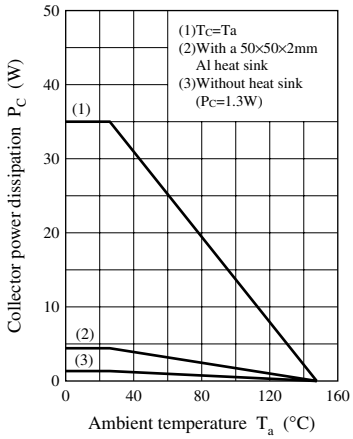
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0937	V_{CEO}	I_C = −30 mA, I_B = 0	−60			V
	2SB0937A			−80			
Base-emitter voltage		V_{BE}	V_{CE} = −4 V, I_C = −2 A			−2.8	V
Collector-base cutoff current (Emitter open)	2SB0937	I_{CBO}	V_{CB} = −60 V, I_E = 0			−1	mA
	2SB0937A		V_{CB} = −80 V, I_E = 0			−1	
Collector-emitter cutoff current (Base open)	2SB0937	I_{CEO}	V_{CE} = −30 V, I_B = 0			−2	mA
	2SB0937A		V_{CE} = −40 V, I_B = 0			−2	
Emitter-base cutoff current (Collector open)		I_{EBO}	V_{EB} = −5 V, I_C = 0			−2	mA
Forward current transfer ratio		h_{FE1}	V_{CE} = −4 V, I_C = −1 A	1000			—
		h_{FE2} *	V_{CE} = −4 V, I_C = −2 A	2000		10000	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C = −2 A, I_B = −8 mA			−2.5	V
Transition frequency		f_T	V_{CE} = −10 V, I_C = −0.5 A, f = 1 MHz		20		MHz
Turn-on time		t_{on}	I_C = −2 A,		0.4		µs
Strage time		t_{stg}	I_{B1} = −8 mA, I_{B2} = 8 mA		1.5		µs
Fall time		t_f	V_{CC} = −50 V		0.5		µs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *: Rank classification

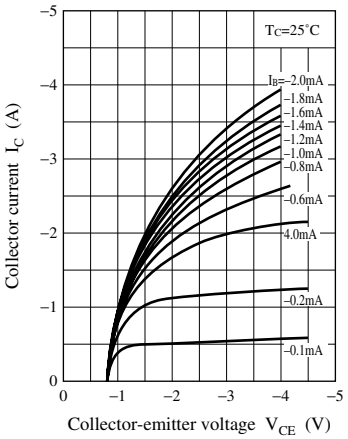
Rank	Q	P
h_{FE1}	2000 to 5000	4000 to 10000

Note) The part number in the parenthesis shows conventional part number.

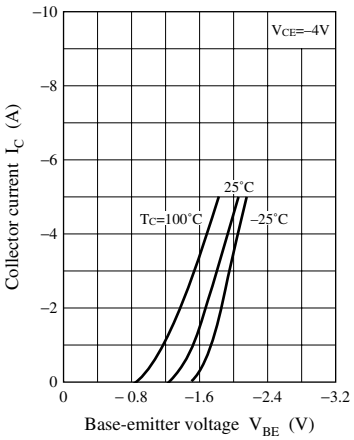
P_C — T_a



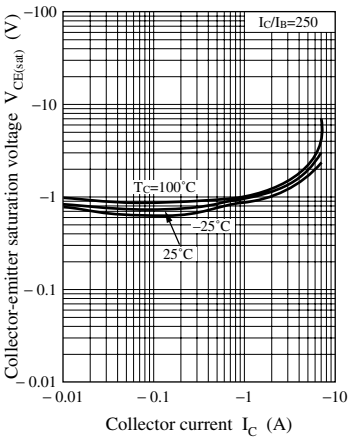
I_C — V_{CE}



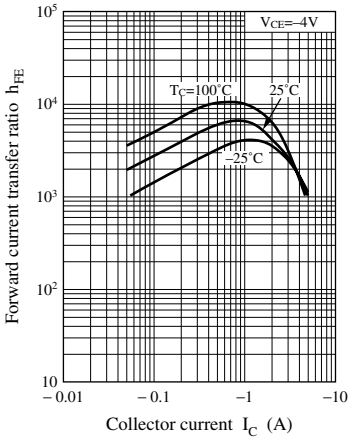
I_C — V_{BE}



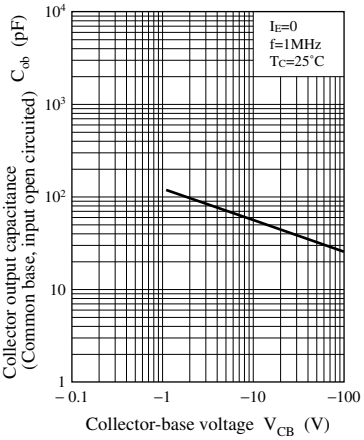
$V_{CE(sat)}$ — I_C



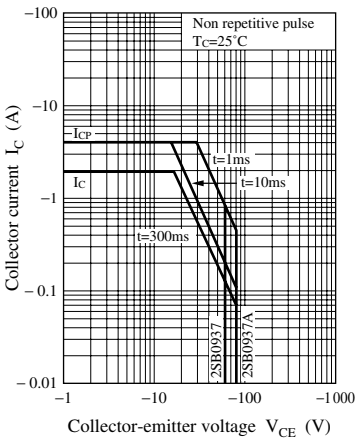
h_{FE} — I_C



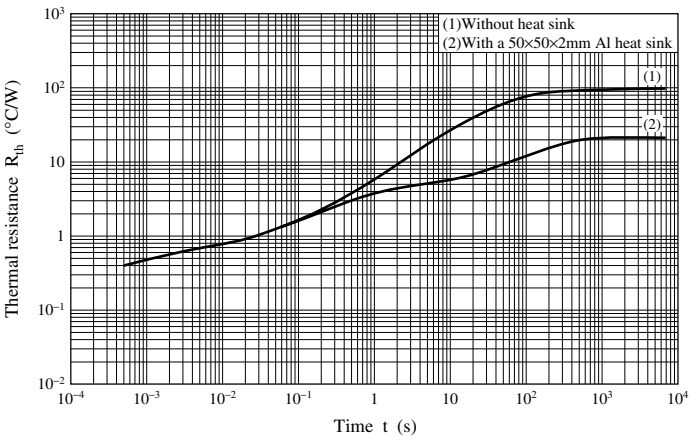
C_{ob} — V_{CB}



Safe operation area



R_{th} — t



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